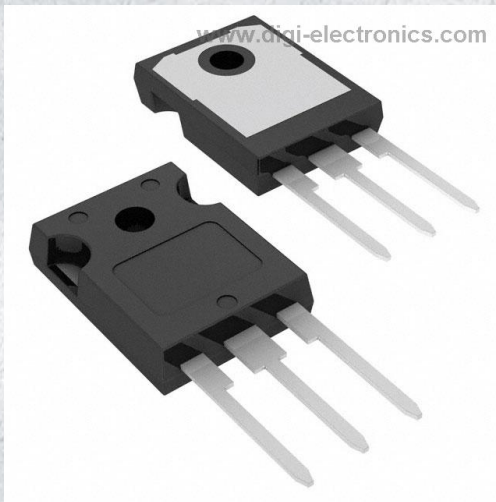


MJH11019G Datasheet



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	MJH11019G-DG
Manufacturer	onsemi
Manufacturer Product Number	MJH11019G
Description	TRANS PNP DARL 200V 15A TO247-3
Detailed Description	Bipolar (BJT) Transistor PNP - Darlington 200 V 15 A 3MHz 150 W Through Hole TO-247-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

MJH11019G

Series:

-

Transistor Type:

PNP - Darlington

Voltage - Collector Emitter Breakdown (Max):

200 V

Current - Collector Cutoff (Max):

1mA

Power - Max:

150 W

Operating Temperature:

-65°C ~ 150°C (TJ)

Package / Case:

TO-247-3

Base Product Number:

MJH11019

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

15 A

Vce Saturation (Max) @ Ib, Ic:

4V @ 150mA, 15A

DC Current Gain (hFE) (Min) @ Ic, Vce:

400 @ 10A, 5V

Frequency - Transition:

3MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-247-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

Not Applicable

ECCN:

EAR99

Complementary Darlington Silicon Power Transistors

MJH11017, MJH11019, MJH11021 (PNP) MJH11018, MJH11020, MJH11022 (NPN)

These devices are designed for use as general purpose amplifiers, low frequency switching and motor control applications.

Features

- High DC Current Gain @ 10 Adc – $h_{FE} = 400$ Min (All Types)
- Collector–Emitter Sustaining Voltage
 - $V_{CEO(sus)} = 150$ Vdc (Min) – MJH11018, 17
 - $= 200$ Vdc (Min) – MJH11020, 19
 - $= 250$ Vdc (Min) – MJH11022, 21
- Low Collector–Emitter Saturation Voltage
 - $V_{CE(sat)} = 1.2$ V (Typ) @ $I_C = 5.0$ A
 - $= 1.8$ V (Typ) @ $I_C = 10$ A
- Monolithic Construction
- These are Pb–Free Devices

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage MJH11018, MJH11017 MJH11020, MJH11019 MJH11022, MJH11021	V_{CEO}	150 200 250	Vdc
Collector–Base Voltage MJH11018, MJH11017 MJH11020, MJH11019 MJH11022, MJH11021	V_{CB}	150 200 250	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	15 30	Adc
Base Current	I_B	0.5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	150 1.2	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	°C

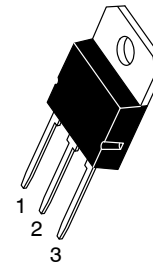
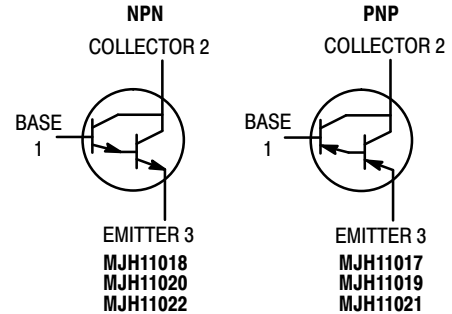
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	0.83	°C/W

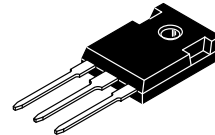
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle $\leq 10\%$.

15 AMPERE DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS 150–250 VOLTS, 150 WATTS



**SOT-93
(TO-218)
CASE 340L
STYLE 1**



**TO-247
CASE 340L
STYLE 3**

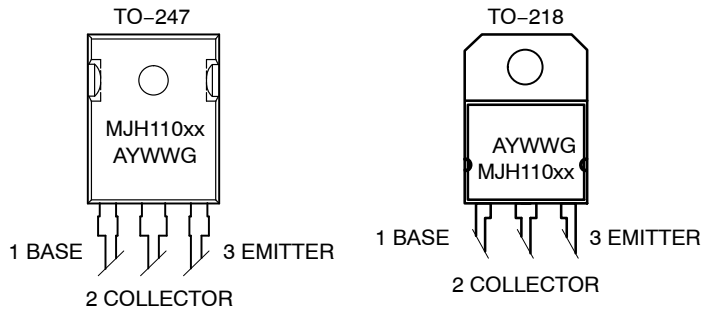
NOTE: Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

ORDERING INFORMATION

See detailed ordering and shipping information in on page 2 of this data sheet.

MJH11017, MJH11019, MJH11021 (PNP) MJH11018, MJH11020, MJH11022 (NPN)

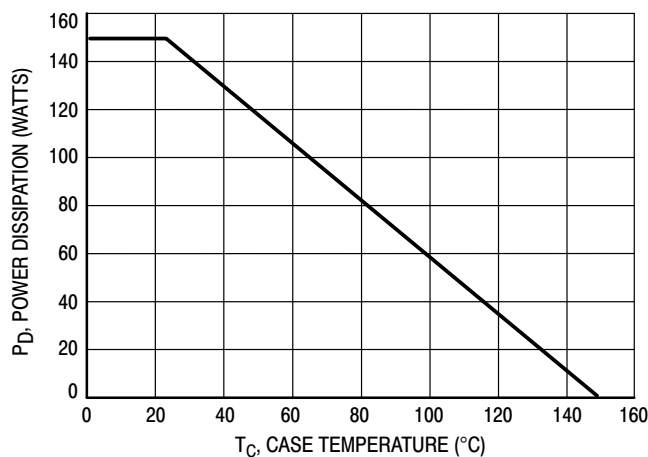
MARKING DIAGRAMS



A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package
 MJH110xx = Device Code
 xx = 17, 19, 21, 18, 20, 22

ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MJH11017G	TO-218 (Pb-Free)	30 Units / Rail
MJH11018G	TO-218 (Pb-Free)	30 Units / Rail
MJH11019G	TO-218 (Pb-Free)	30 Units / Rail
MJH11020G	TO-218 (Pb-Free)	30 Units / Rail
MJH11021G	TO-218 (Pb-Free)	30 Units / Rail
MJH11022G	TO-218 (Pb-Free)	30 Units / Rail
MJH11017G	TO-247 (Pb-Free)	30 Units / Rail
MJH11018G	TO-247 (Pb-Free)	30 Units / Rail
MJH11019G	TO-247 (Pb-Free)	30 Units / Rail
MJH11020G	TO-247 (Pb-Free)	30 Units / Rail
MJH11021G	TO-247 (Pb-Free)	30 Units / Rail
MJH11022G	TO-247 (Pb-Free)	30 Units / Rail

MJH11017, MJH11019, MJH11021 (PNP) MJH11018, MJH11020, MJH11022 (NPN)**Figure 1. Power Derating****ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 2) ($I_C = 0.1 \text{ Adc}$, $I_B = 0$)	$V_{CE(sus)}$	150 200 250	- - -	Vdc
Collector Cutoff Current ($V_{CE} = 75 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 100 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 125 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	- - -	1.0 1.0 1.0	mAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CB}$, $V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = \text{Rated } V_{CB}$, $V_{BE(off)} = 1.5 \text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_{CEV}	- -	0.5 5.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	2.0	mAdc

ON CHARACTERISTICS (Note 2)

DC Current Gain ($I_C = 10 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 15 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	400 100	15,000 -	-
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ Adc}$, $I_B = 100 \text{ mA}$) ($I_C = 15 \text{ Adc}$, $I_B = 150 \text{ mA}$)	$V_{CE(sat)}$	- -	2.5 4.0	Vdc
Base-Emitter On Voltage ($I_C = 10 \text{ A}$, $V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(on)}$	-	2.8	Vdc
Base-Emitter Saturation Voltage ($I_C = 15 \text{ Adc}$, $I_B = 150 \text{ mA}$)	$V_{BE(sat)}$	-	3.8	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain Bandwidth Product ($I_C = 10 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	f_T	3.0	-	-
Output Capacitance MJH11018, MJH11020, MJH11022 ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$) MJH11017, MJH11019, MJH11021	C_{ob}	- -	400 600	pF
Small-Signal Current Gain ($I_C = 10 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	75	-	-

SWITCHING CHARACTERISTICS

Characteristic	Symbol	Typical		Unit
		NPN	PNP	
Delay Time	t_d	150	75	ns
Rise Time	t_r	1.2	0.5	μs
Storage Time	t_s	4.4	2.7	μs
Fall Time	t_f	2.5	2.5	μs

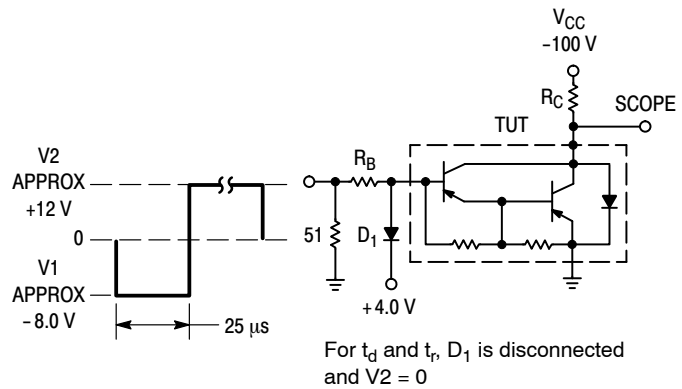
$(V_{CC} = 100 \text{ V}$, $I_C = 10 \text{ A}$, $I_B = 100 \text{ mA}$, $V_{BE(off)} = 5.0 \text{ V}$) (See Figure 2)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

MJH11017, MJH11019, MJH11021 (PNP) MJH11018, MJH11020, MJH11022 (NPN)

R_B & R_C varied to obtain desired current levels
 D_1 , must be fast recovery types, e.g.:
 1N5825 used above $I_B \approx 100$ mA
 MSD6100 used below $I_B \approx 100$ mA



$t_r, t_f \leq 10$ ns
 Duty Cycle = 1.0% For NPN test circuit, reverse diode and voltage polarities.

Figure 2. Switching Times Test Circuit

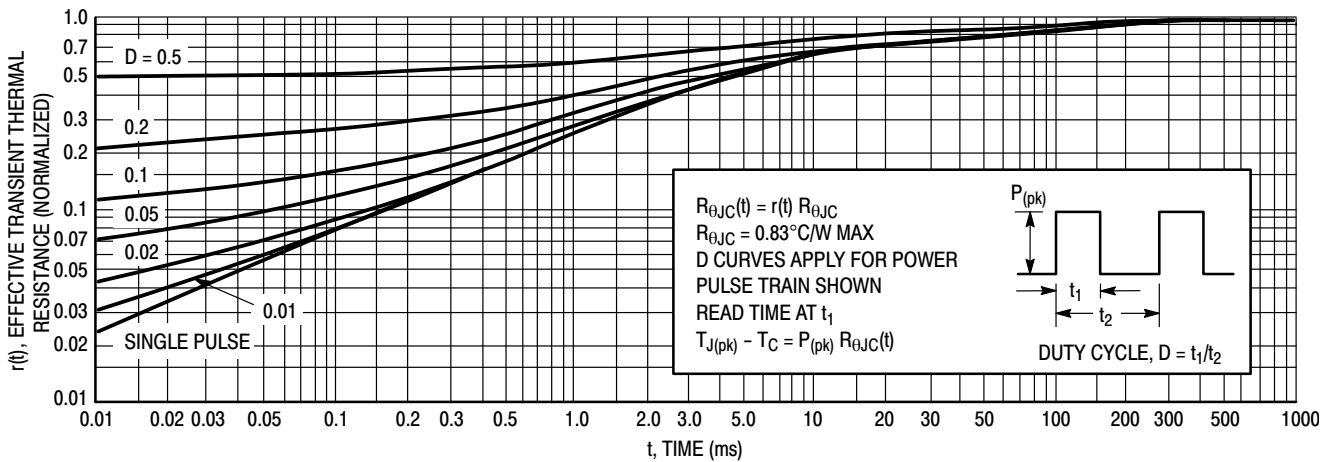


Figure 3. Thermal Response

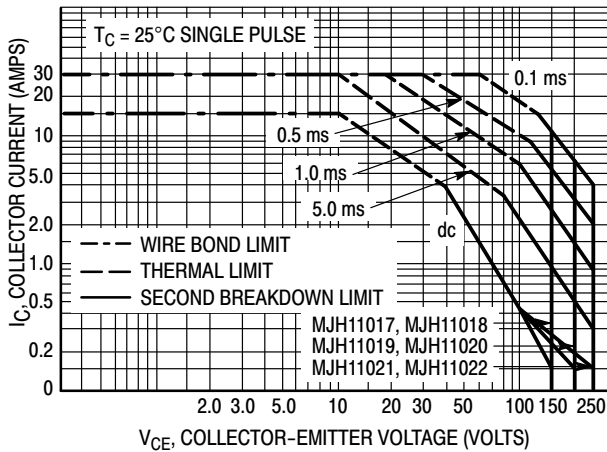


Figure 4. Maximum Rated Forward Bias Safe Operating Area (FBSOA)

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 4 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 3. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJH11017, MJH11019, MJH11021 (PNP) MJH11018, MJH11020, MJH11022 (NPN)

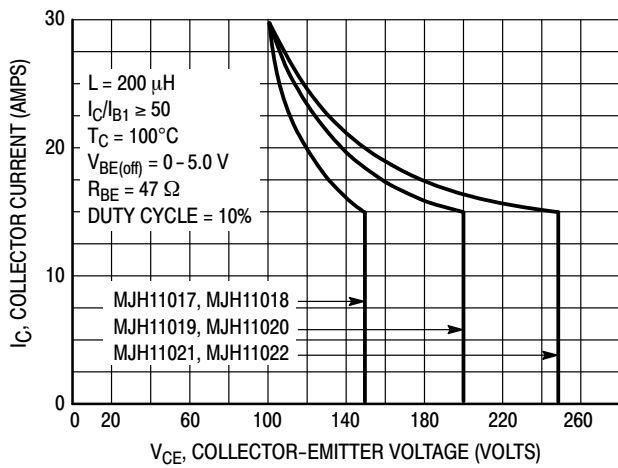


Figure 5. Maximum Rated Reverse Bias Safe Operating Area (RBSOA)

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current conditions during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 5 gives RBSOA characteristics.

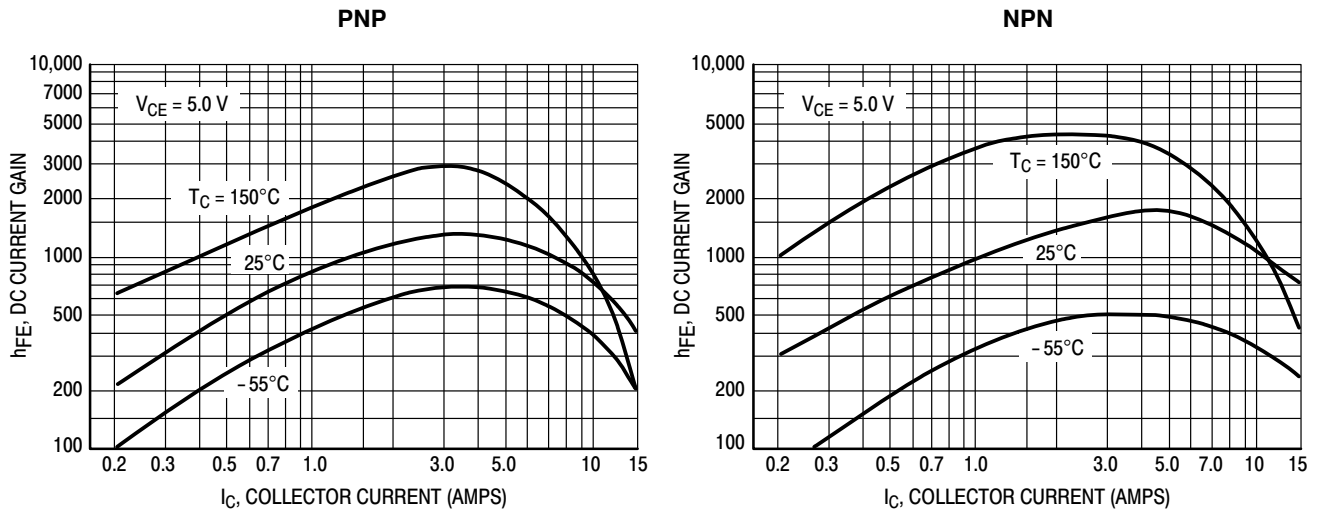


Figure 6. DC Current Gain

MJH11017, MJH11019, MJH11021 (PNP) MJH11018, MJH11020, MJH11022 (NPN)

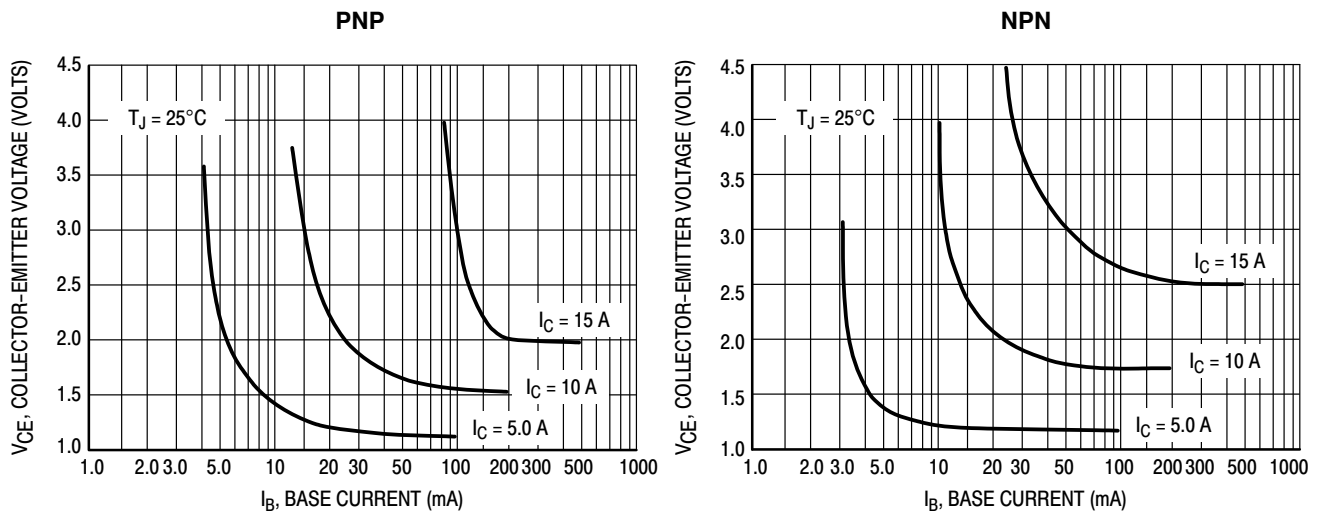


Figure 7. Collector Saturation Region

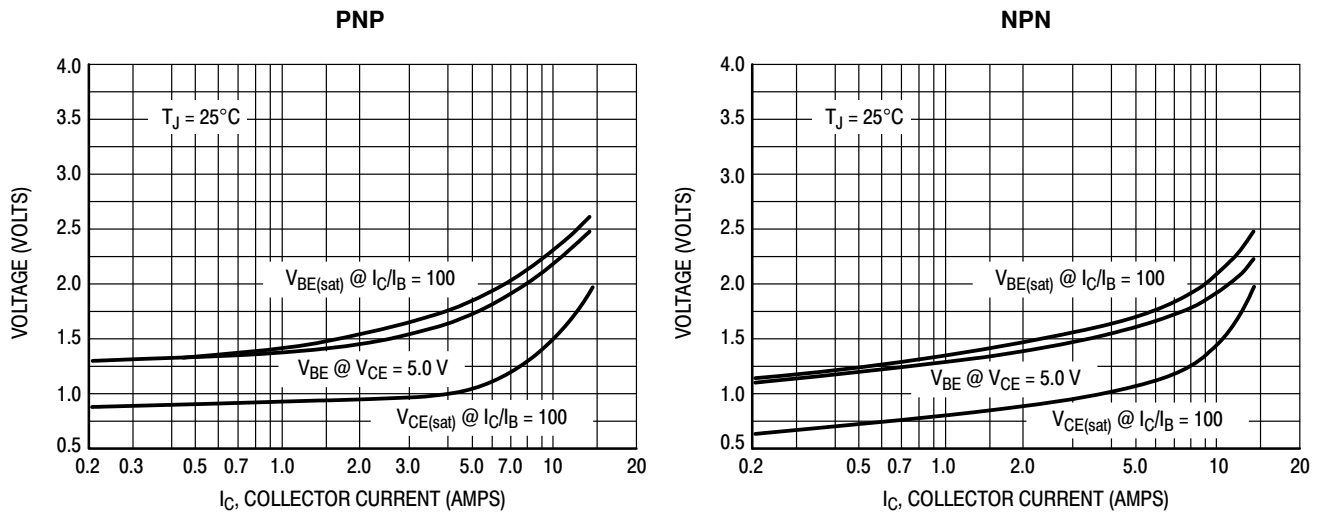


Figure 8. "On" Voltages

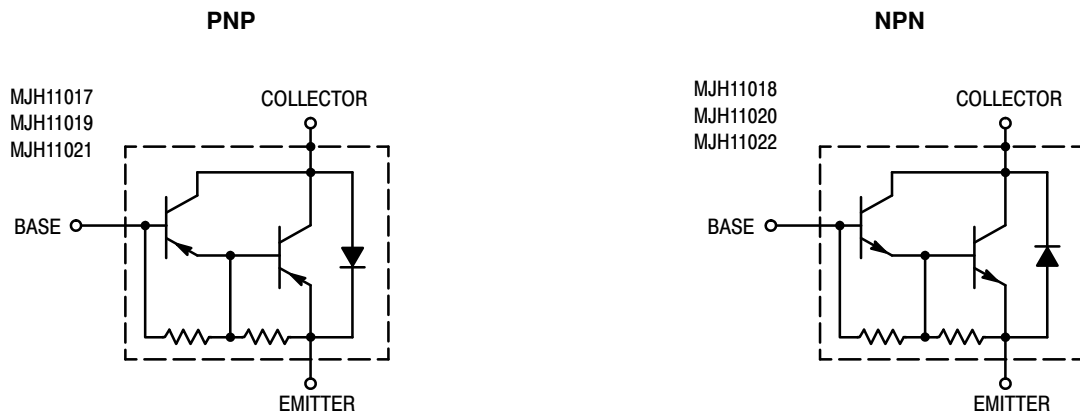


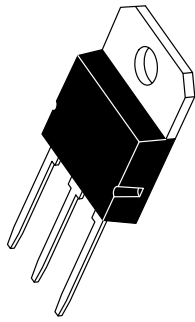
Figure 9. Darlington Schematic



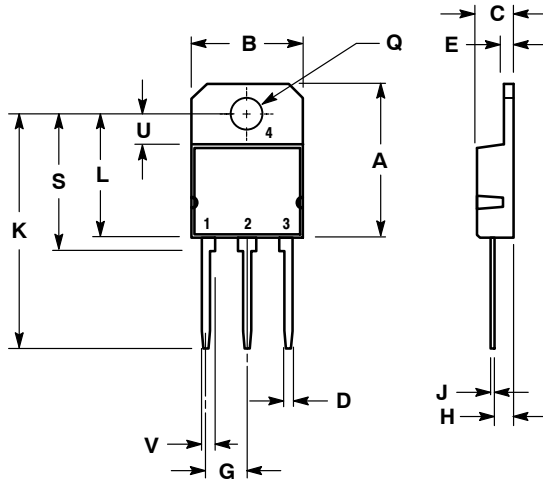
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**

**SOT-93 (TO-218)
CASE 340D-02
ISSUE E**

DATE 03 JAN 2002



SCALE 1:1



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

GENERIC MARKING DIAGRAM*



A = Assembly Location
Y = Year
WW = Work Week
XXXXX = Device Code

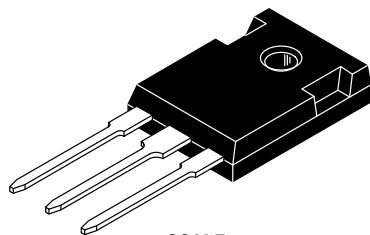
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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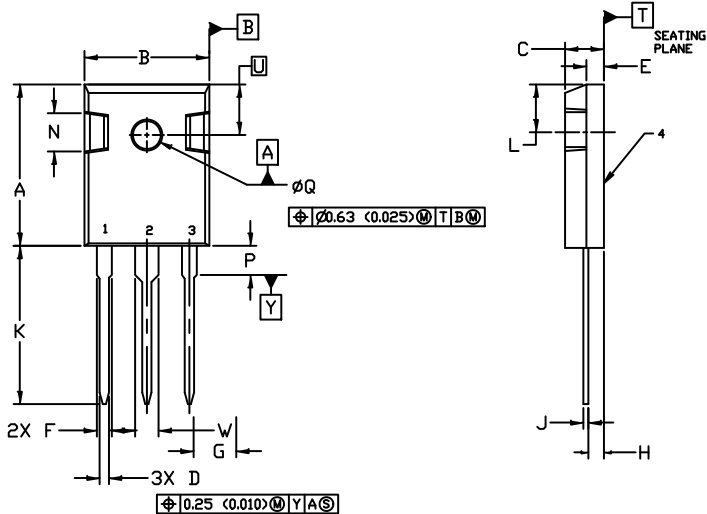
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



**TO-247
CASE 340L
ISSUE G**

DATE 06 OCT 2021

SCALE 1:1

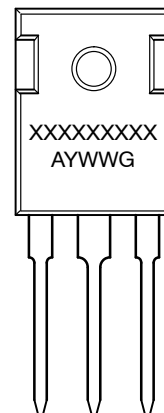


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER

DIM	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45	BSC	0.215	BSC
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	----	4.50	----	0.177
Q	3.55	3.65	0.140	0.144
U	6.15	BSC	0.242	BSC
W	2.87	3.12	0.113	0.123

**GENERIC
MARKING DIAGRAM***



- | | | | |
|--|--|--|--|
| <p>STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN</p> | <p>STYLE 2:
PIN 1. ANODE
2. CATHODE (S)
3. ANODE 2
4. CATHODES (S)</p> | <p>STYLE 3:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> | <p>STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> |
| <p>STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE</p> | <p>STYLE 6:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2</p> | | |

- XXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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